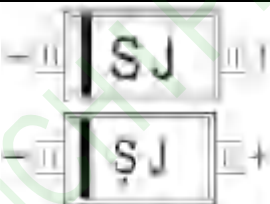
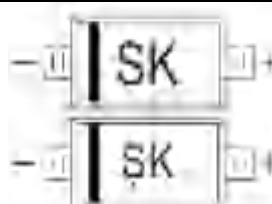
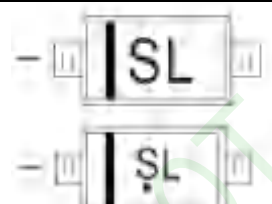


B5817W-B5819W SCHOTTKY BARRIER DIODE

Features:

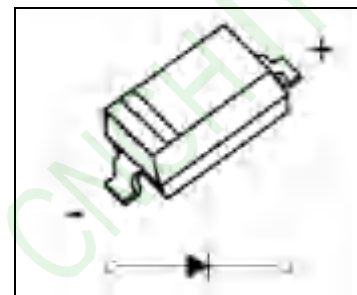
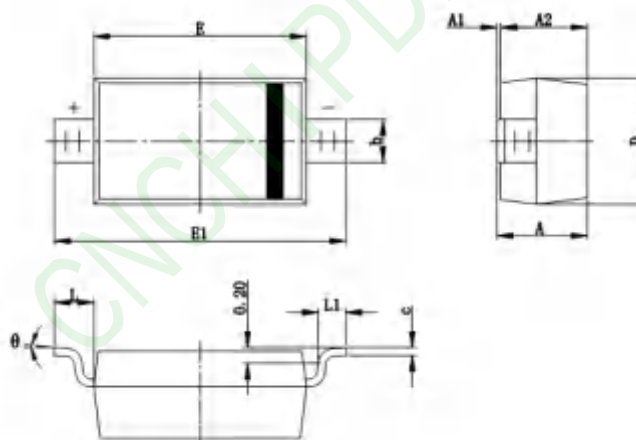
- For use in low voltage, high frequency inverters
- Free wheeling, and polarity protection applications.

Marking:

B5817W:SJ	B5818W:SK	B5819W:SL
		

The marking bar indicates the cathode

Solid dot = Green molding compound device, if none, the normal device.


Mechanical Dimensions: In mm/Inches


Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	0.050	0.250	0.004	0.010
A1	0.000	0.500	0.000	0.020
A2	0.050	0.150	0.004	0.006
b	0.450	0.650	0.018	0.026
c	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
E	2.800	2.800	0.110	0.110
E1	3.050	3.050	0.120	0.120
L	0.900 REF		0.035 REF	
L1	0.250	0.450	0.010	0.018
B	0"	6"	0"	0.240"

SOD-123

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •



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Email: sales@cnchipdepot.com

Website: www.cnchipdepot.com

Address: B705, Baihe Commercial Building, Xiangge Rd, Longgang, Shenzhen 518112, China

Product Portfolio

Primary Category	Secondary Category	Series	Model	Package	Link
Diode	Rectifier Diode	1N4007	1N4007	SMA(DO-214AC)	https://www.cnchipdepot.com/p/fosan-1n4007-107172.html
Diode	Rectifier Diode	1N4007	1N4007	SOD-123FL	https://www.cnchipdepot.com/p/fosan-1n4007-107173.html
Diode	Switching Diode	BAW56	BAW56	SOT-23	https://www.cnchipdepot.com/p/fosan-baw56-107174.html
Diode	Switching Diode	BAW56	BAW56W-6AF	SOT-323	https://www.cnchipdepot.com/p/fosan-baw56w-6af-107175.html

Diode	Switching Diode	1N4148	1N4148WT	SOD-323	https://www.cnchipdepot.com/p/fosan-1n4148wt-107176.html
Diode	Schottky Diode	1N5819	1N4148WS	SOD-323	https://www.cnchipdepot.com/p/fosan-1n4148ws-107177.html
Diode	Schottky Diode	SS34	SS34	SMA(DO-214AC)	https://www.cnchipdepot.com/p/fosan-ss34-107178.html
Diode	Schottky Diode	SS54	SS34B	SMA(DO-214AC)	https://www.cnchipdepot.com/p/baocheng-ss34b-12183.html
Diode	Schottky Diode	SS14	SS34C	SMA(DO-214AC)	https://www.cnchipdepot.com/p/baocheng-ss34c-12188.html
Diode Fast Recovery / High Efficiency Diode		US1M	US1M	SMA	https://www.cnchipdepot.com/p/fosan-us1m-107198.html
Diode Fast Recovery / High Efficiency Diode		US1M	US1MA-AAF	SMA	https://www.cnchipdepot.com/p/fosan-us1ma-aaf-107179.html
Diode Fast Recovery / High Efficiency Diode		US1M	US1MF	SMAF	https://www.cnchipdepot.com/p/baocheng-us1mf-17709.html
Diode	Switching Diode	BAV99	BAV99	SOT-23	https://www.cnchipdepot.com/p/agertech-bav99-18862.html
Diode	Switching Diode	BAV99	BAV99-6AF	SOT-23	https://www.cnchipdepot.com/p/fosan-ss34-107178.html
Diode	Switching Diode	BAV99	BAV99W-6AF	SOT-23	https://www.cnchipdepot.com/p/fosan-bav99w-6af-107181.html
Diode	Schottky Diode	B5819W	B5819WS	SOD-123	https://www.cnchipdepot.com/p/am-b5819ws-12167.html
Diode	Schottky Diode	B5819W	B5819W		https://www.cnchipdepot.com/p/am-b5819w-12166.html
Transistor (BJT)	NPN BJT	S8050	S8050	SOT-23	https://www.cnchipdepot.com/p/am-s8050-1108.html

Transistor (BJT)	NPN BJT	S8050	S8050-6AF	SOT-23	https://www.cnchipdepot.com/p/fosan-s8050-6af-107182.html
Transistor (BJT)	NPN BJT	SS8050	SS8050	SOT-23	https://www.cnchipdepot.com/p/alj-longjing-micro-s8050-1087.html
Transistor (BJT)	NPN BJT	SS8050	SS8050S	SOT-23	https://www.cnchipdepot.com/p/fosan-ss8050s-2326.html
Transistor (BJT)	NPN BJT	MMBT5551	MMBT5551	SOT-23	https://www.cnchipdepot.com/p/agertech-mmbt5551-1003.html
Transistor (BJT)	NPN BJT	MMBT5551	MMBT5551S	SOT-23	https://www.cnchipdepot.com/p/fosan-mmbt5551s-2327.html
Transistor (BJT)	NPN BJT	MMBT5551	MMBT5551-6AF	SOT-23	https://www.cnchipdepot.com/p/fosan-mmbt5551-6af-107183.html
Transistor	MOSFET	7002	2N7002	SOT-23	https://www.cnchipdepot.com/p/fosan-2n7002-107184.html
Transistor	MOSFET	7002	2N7002K	SOT-23	https://www.cnchipdepot.com/p/alj-longjing-micro--2n7002k-5083.html
Transistor	MOSFET	7002	2N7002K-6AF	SOT-23	https://www.cnchipdepot.com/p/fosan-2n7002k-6af-107185.html
Transistor	MOSFET	7002	2N7002-6AF	SOT-23	https://www.cnchipdepot.com/p/fosan-2n7002-6af-107186.html
Transistor	MOSFET	BSS84	BSS84	SOT-23	https://www.cnchipdepot.com/p/fosan-bss84-107187.html
Transistor	MOSFET	BSS84	BSS84-6AF	SOT-363	https://www.cnchipdepot.com/p/fosan-bss84-6af-107188.html
Transistor (BJT)	NPN BJT	BC847	BC847A	SOT-23	https://www.cnchipdepot.com/p/alj-longjing-micro--bc847a-1052.html
Transistor (BJT)	NPN BJT	BC847	BC847B	SOT-23	https://www.cnchipdepot.com/p/alj-longjing-micro--bc847b-1056.html

Transistor (BJT)	NPN BJT	BC847	BC847C	SOT-23	https://www.cnchipdepot.com/p/alj-longjing-micro--bc847c-1055.html
Power IC	LDO	1117	LD1117-3.3	SOT223	https://www.cnchipdepot.com/p/hxy-mosfet-huaxuan-yang-electronics--ld1117-3-3-25490.html
Power IC	LDO	1117	LD1117-1.8	SOT223	https://www.cnchipdepot.com/p/hxy-mosfet-huaxuan-yang-electronics--ld1117-1-8-25429.html
Power IC	LDO	1117	LD1117-5.0	SOT223	https://www.cnchipdepot.com/p/hxy-mosfet-huaxuan-yang-electronics--ld1117-5-0-25444.html
Power IC	LDO	1117	LD1117-ADJ	SOT223	https://www.cnchipdepot.com/p/hxy-mosfet-huaxuan-yang-electronics--ld1117-adj-25427.html

Ordering Information:

Device	Package	Shipping
B5817W-5819W	SOD-123(Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings @T_A=25°C unless otherwise specified

Parameter	Symbol	B5817W	B5818W	B5819W	Unit
Non-Repetitive Peak Reverse Voltage	V _{RM}	20	30	40	
Peak Repetitive Reverse Voltage	V _{RRM}	20	30	40	V
Working Peak Reverse Voltage	V _{RWM}				
DC Blocking Voltage	V _R				
RMS Reverse Voltage	V _{R(RMS)}	14	21	28	V
Average Rectified Output Current	I _O	1			A
Non-repetitive Peak Forward Surge Current @t=8.3ms	I _{FSM}	9			A
Repetitive Peak Forward Current	I _{FRM}	1.5			A
Power Dissipation	P _D	500			mW
Thermal Resistance from Junction to Ambient	R _{θJA}	200			°C/W
Junction Temperature	T _j	125			°C
Storage Temperature	T _{stg}	-55~+150			°C

Electrical Characteristics @T_A=25°C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V _(BR)	I _R =1mA B5817W B5818W B5819W	20 30 40	- - -	V
Reverse voltage leakage current	I _R	V _R =20V B5817W V _R =30V B5818W V _R =40V B5819W	-	1	mA
Forward voltage	V _F	B5817W I _F =1A I _F =3A B5818W I _F =1A I _F =3A B5819W I _F =1A I _F =3A	- - -	0.45 0.75 0.55 0.875 0.60 0.90	V
Diode capacitance	C _D	V _R =4V, f=1MHz	-	120	pF

